



2015 Advanced Lithography :

Measuring Aberrations using EUV Mask Roughness

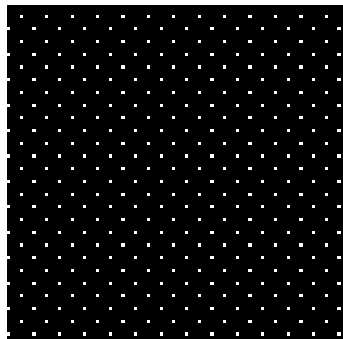
Rene Claus

Markus Benk, Antoine Wojdyla, Alex Donoghue,
David Johnson, Kenneth Goldberg, Andrew Neureuther,
Patrick Naulleau, and Laura Waller

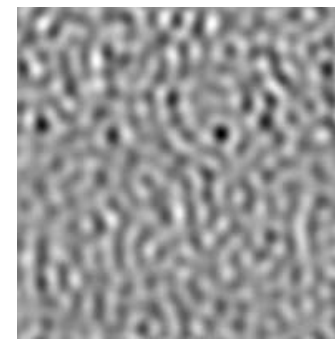
Measuring Aberrations with Roughness

- Aberrations change the results from an EUV actinic inspection system
 - Want to measure aberrations
 - Want to measure from images directly
- Could use a programmed object (ex: contact array)
- We present a way to use existing mask roughness
 - Aberrations can be measured on any mask

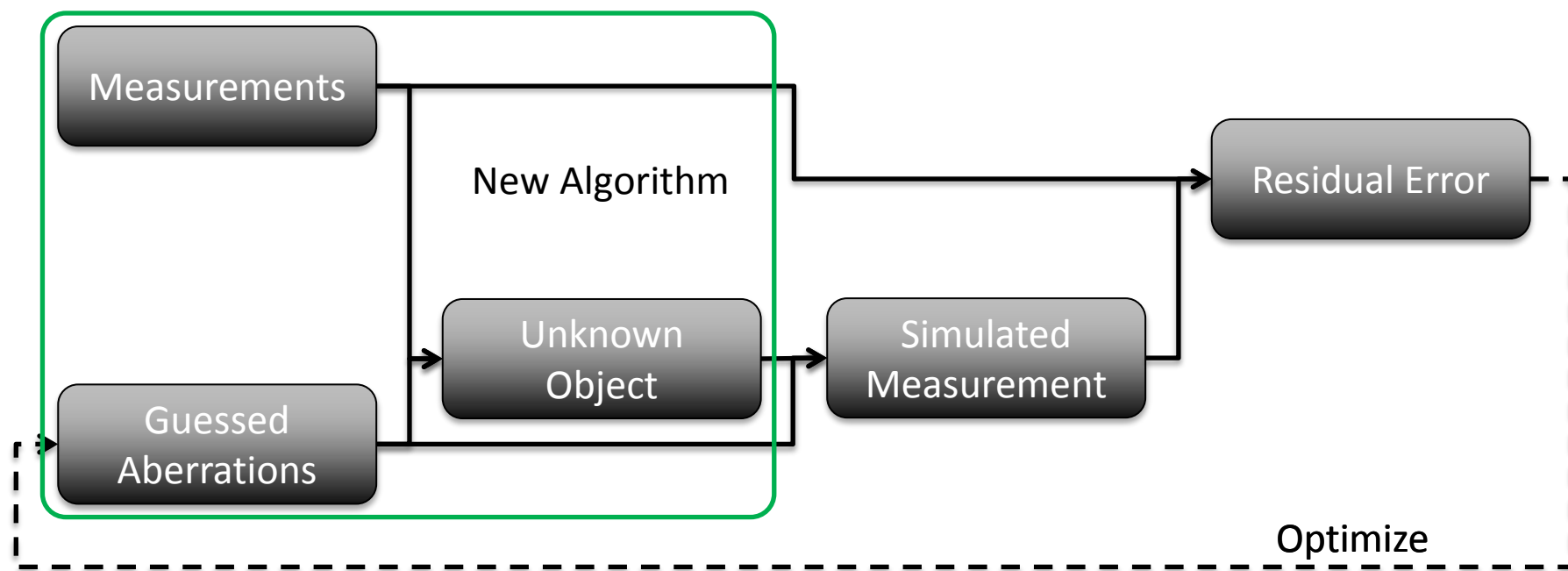
Programmed Test Object



Existing Mask Roughness

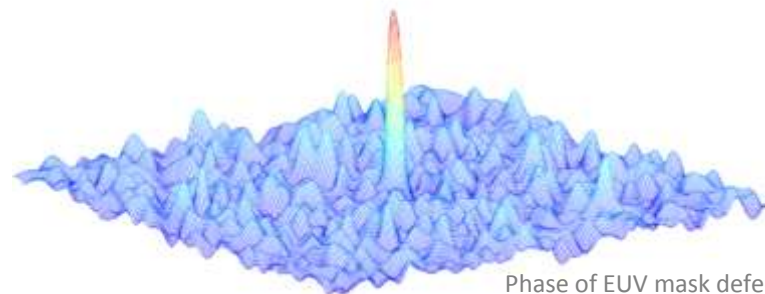
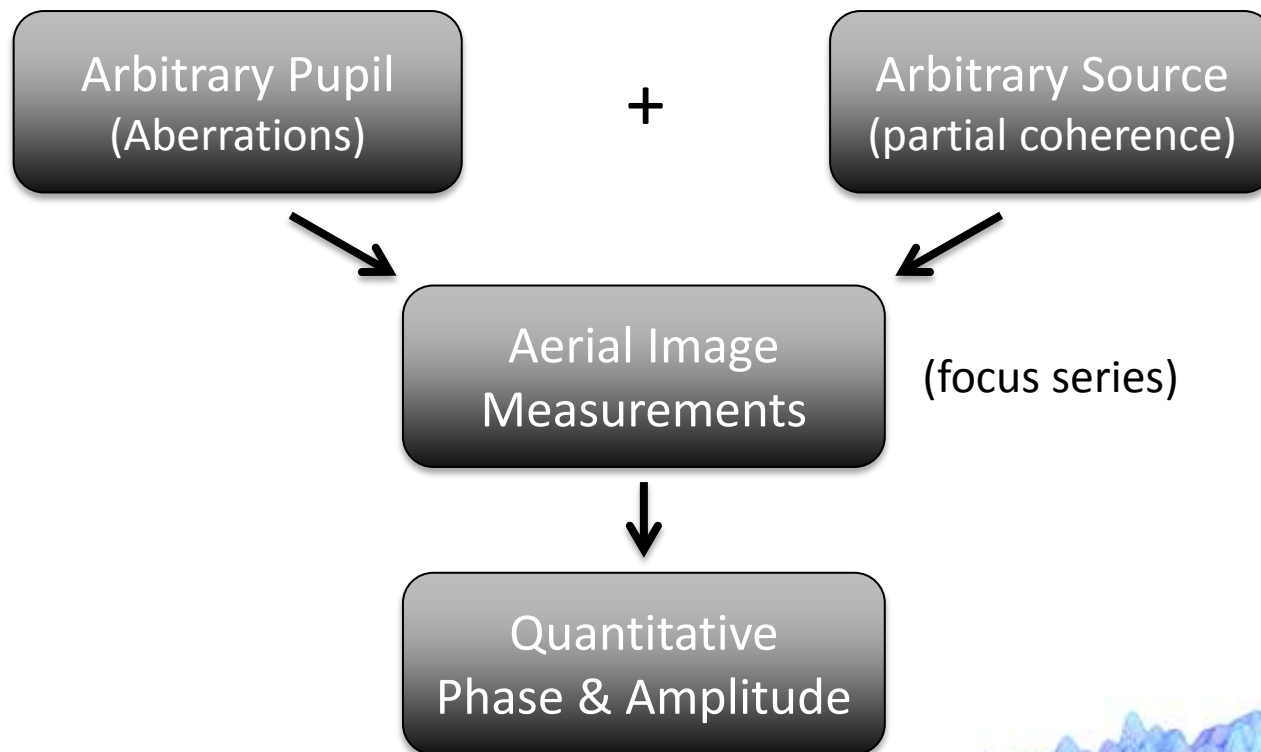


Measuring Aberrations



- Unknown test object
 - Calculate object from model + measurements
- Unknown aberrations
- Minimize residual error by guessing different aberrations

New Phase Retrieval Algorithm

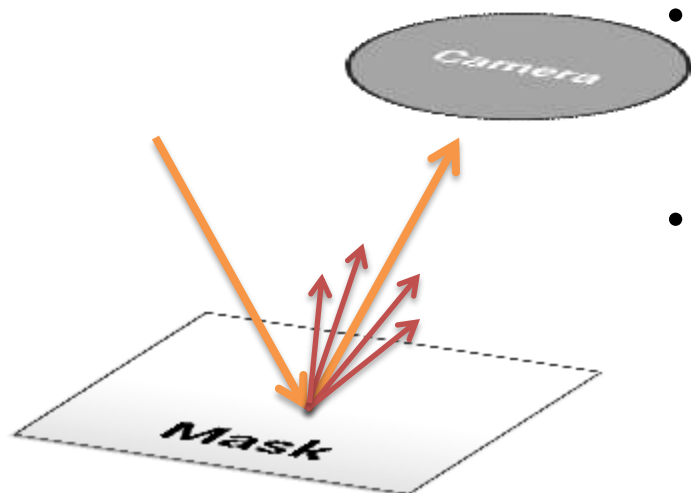


Phase of EUV mask defect

More details in:

R. Claus, "Phase Measurements of EUV Masks," SPIE Advanced Lithography (2015).

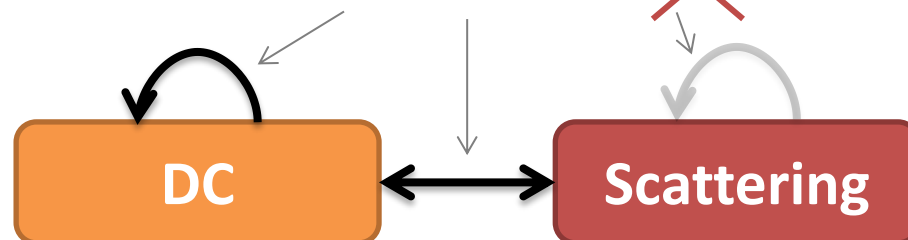
Weak Object Assumption



- Consider a rough mirror (or mask)
 - Most of the light is reflected
 - Some of the light is scattered
- The electric field leaving the mask can be expressed as the sum of these components

$$E = 1 + E_s$$

$$I = |1 + E_s|^2 = 1 + 2\text{Re}\{E_s\} + \cancel{|E_s|^2}$$



- For most objects $\text{Scattering} \ll \text{DC}$
 - We can ignore *Scattering-Scattering*

Recovering the Field

Write the intensity as a sum of convolutions:

$$I = 1 + E_{re} * K_{re} + E_{im} * K_{im} + O(|E_s|^2)$$



$$\tilde{I} = 1 + \widetilde{E}_{re} \cdot \widetilde{K}_{re} + \widetilde{E}_{im} \cdot \widetilde{K}_{im}$$



$$\begin{bmatrix} \tilde{I}_1(f_i) \\ \vdots \\ \tilde{I}_n(f_i) \end{bmatrix} = \begin{bmatrix} \widetilde{K}_{re}^1(f_i) & \widetilde{K}_{im}^1(f_i) \\ \vdots & \vdots \\ \widetilde{K}_{re}^n(f_i) & \widetilde{K}_{im}^n(f_i) \end{bmatrix} \begin{bmatrix} \widetilde{E}_{re}(f_i) \\ \widetilde{E}_{im}(f_i) \end{bmatrix}$$

Linear system of equations →
solve with least squares

Transfer functions:

$$\begin{aligned} \widetilde{K}_{re} &= (P \cdot L) \star P + P \star (P \cdot L) \\ \widetilde{K}_{im} &= (P \cdot L) \star P - P \star (P \cdot L) \end{aligned}$$

P : pupil function, L : source shape



consider aberrations



use partial coherence

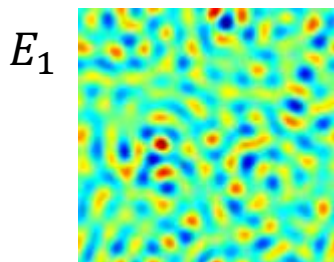
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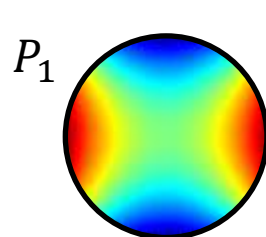
Aberration and Coherent Imaging

- Under coherent illumination, the object & aberrations are not linearly independent
- Partial coherence can solve the problem

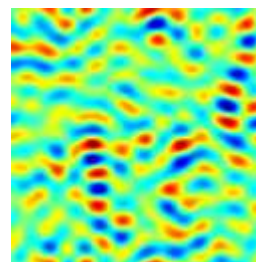
Isotropic Roughness



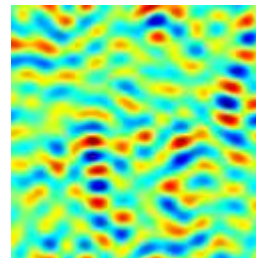
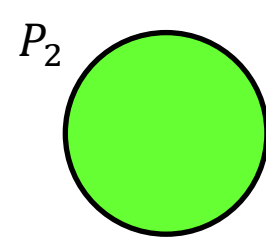
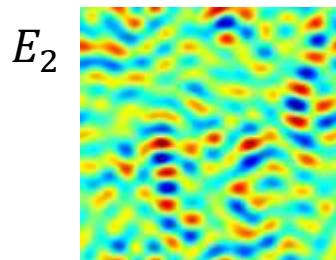
Aberrated Pupil



Aberrated Looking Speckle



$$I = |E_1 * P_1|^2$$



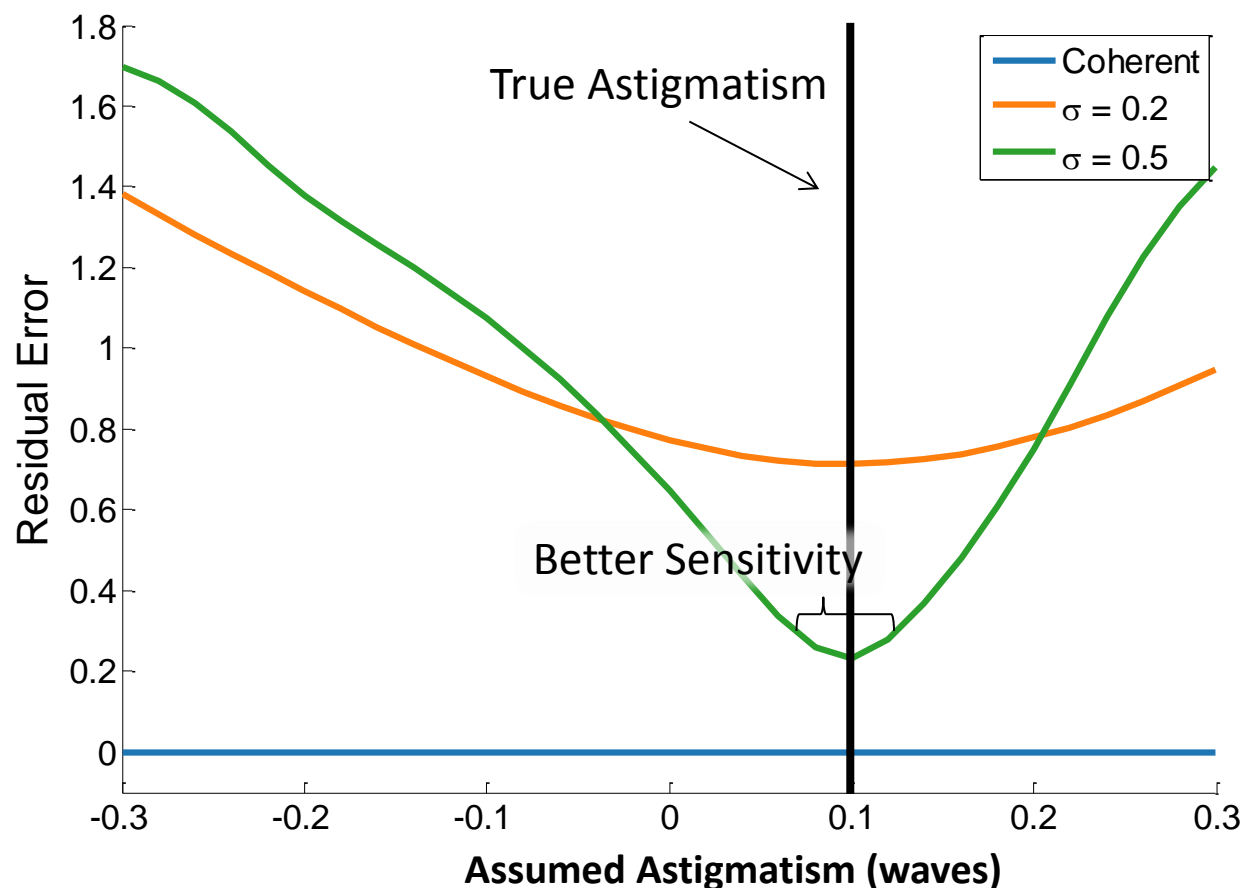
$$I = |E_2 * P_2|^2$$

Directional Roughness

Perfect Pupil

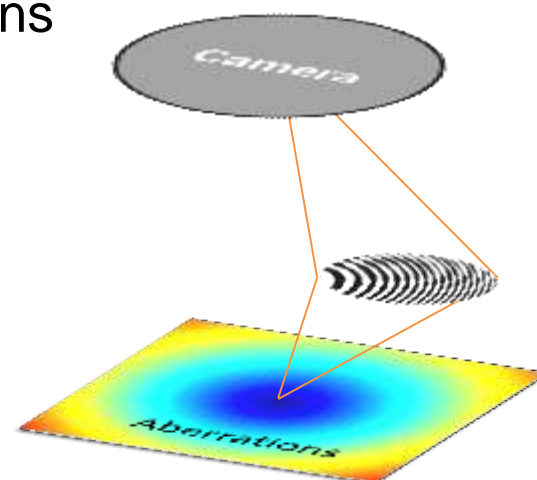
Partial Coherence Improves Sensitivity

Simulated 21 through-focus images of speckle with astigmatism:

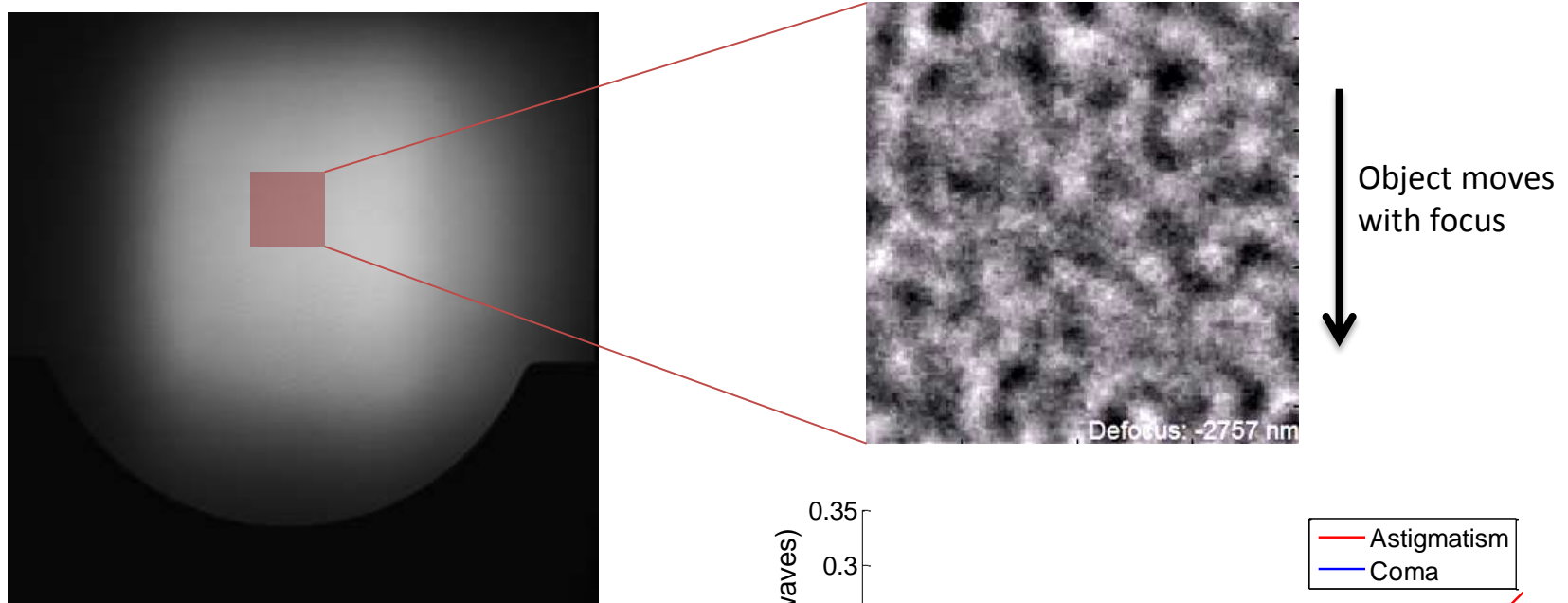


SEMATECH Berkeley SHARP

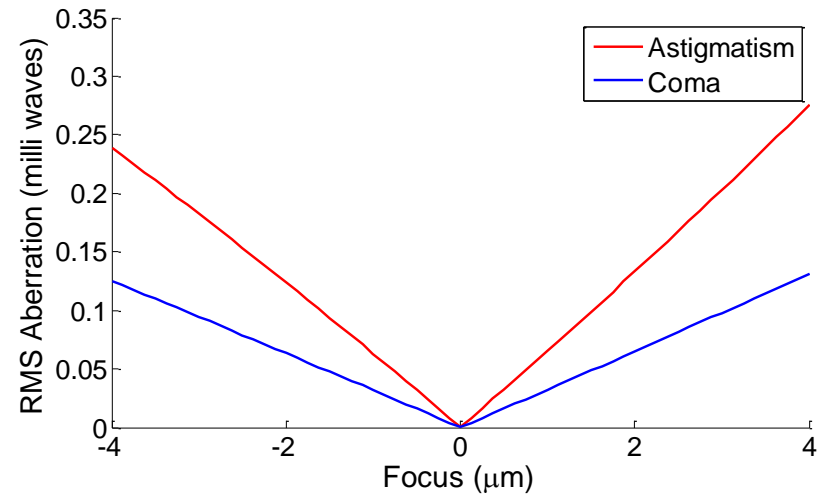
- Actinic mask inspection system at LBNL
- Zone plate lens as objective
 - + Less expensive than multilayer optics
 - + Easy to test different lenses
 - Single lens system
 - Strong field dependent aberrations
 - Aberrations vary with focus



Aberrations Vary With Focus

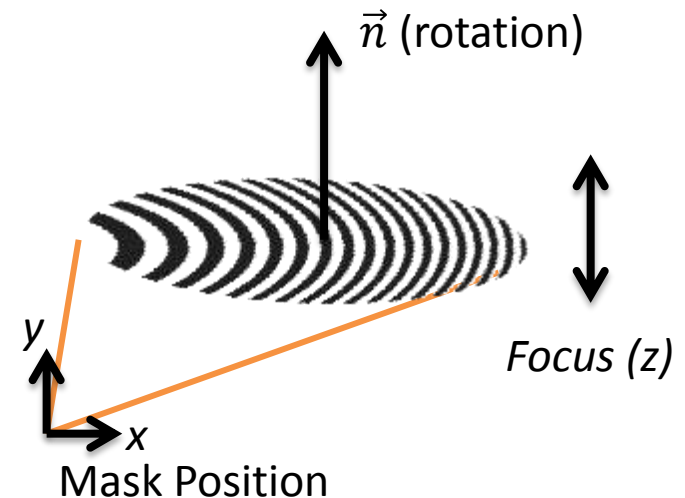


Aberration is not constant with focus

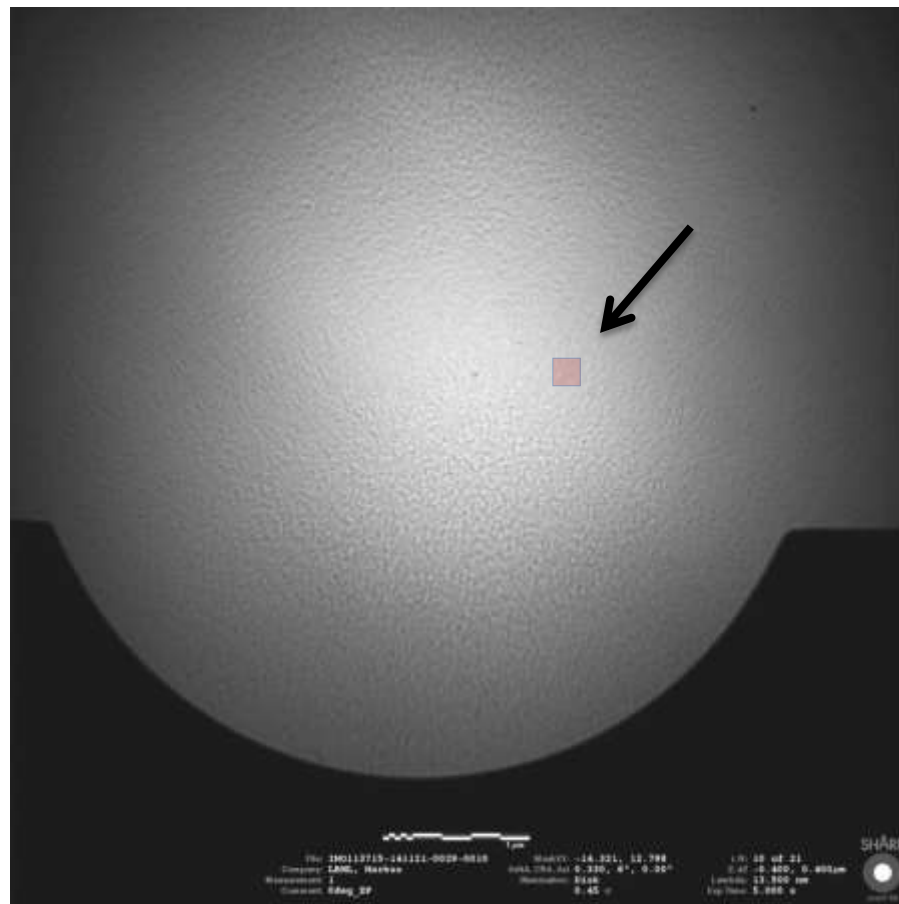


Modeling the Zone Plate

- Instead of modeling aberrations at each position we model the zone plate
 - rotation of zone plate
 - position of zone plate
 - illumination angle
- Calculate aberrations using ray tracing
- Consider physical measurement
 - “Zone plate was moved 500nm up per image”
 - Captures how aberrations change in each image
 - Captures how object moves
- Fewer parameters to optimize



Calibrating the Zone Plate



Illumination: $\sigma = 0.25$, monopole

Examine small areas →
aberrations are approx constant

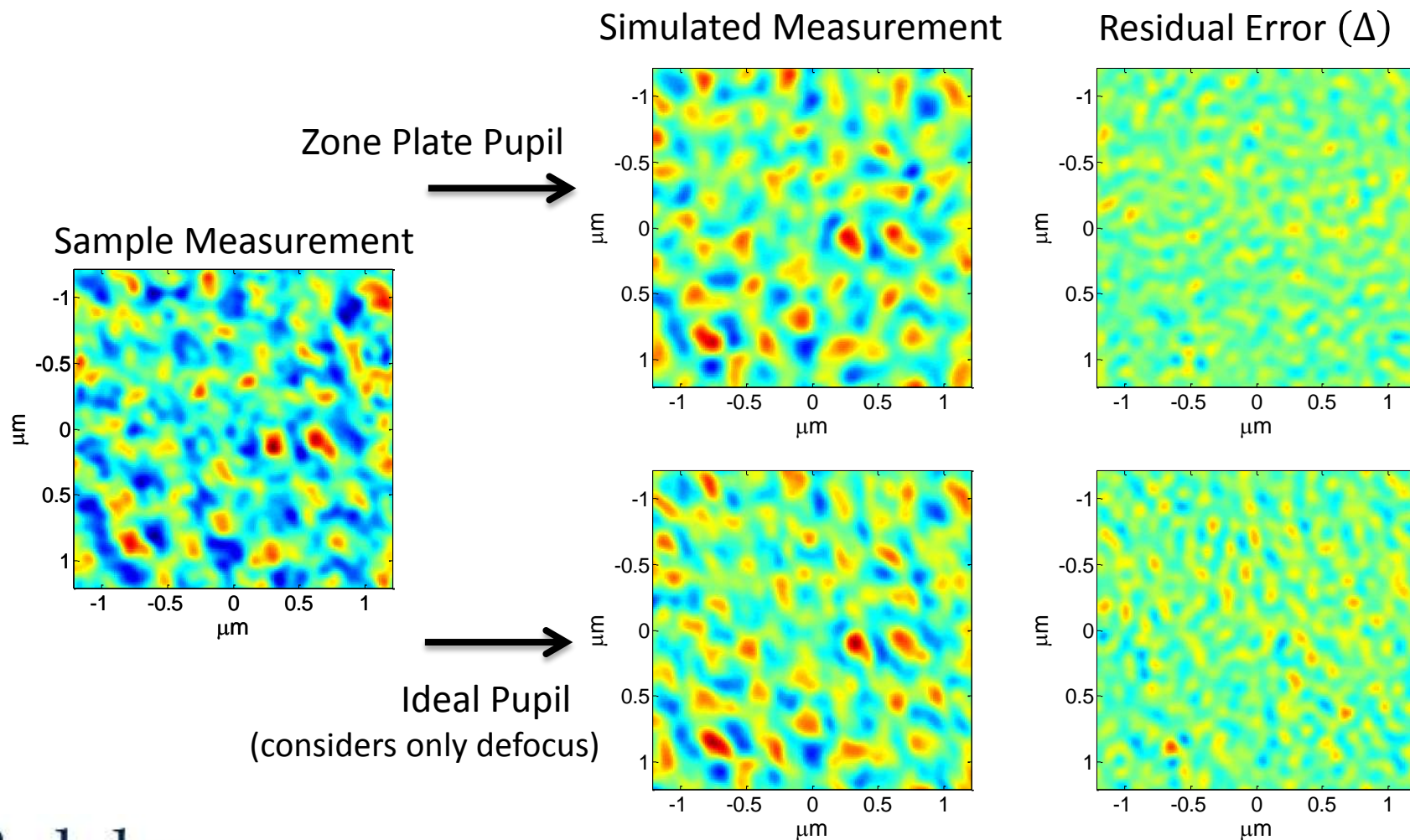
- Where is the center of the field?
- What is the tip/tilt of the zone plate?

Wasn't able to automatically optimize the parameters

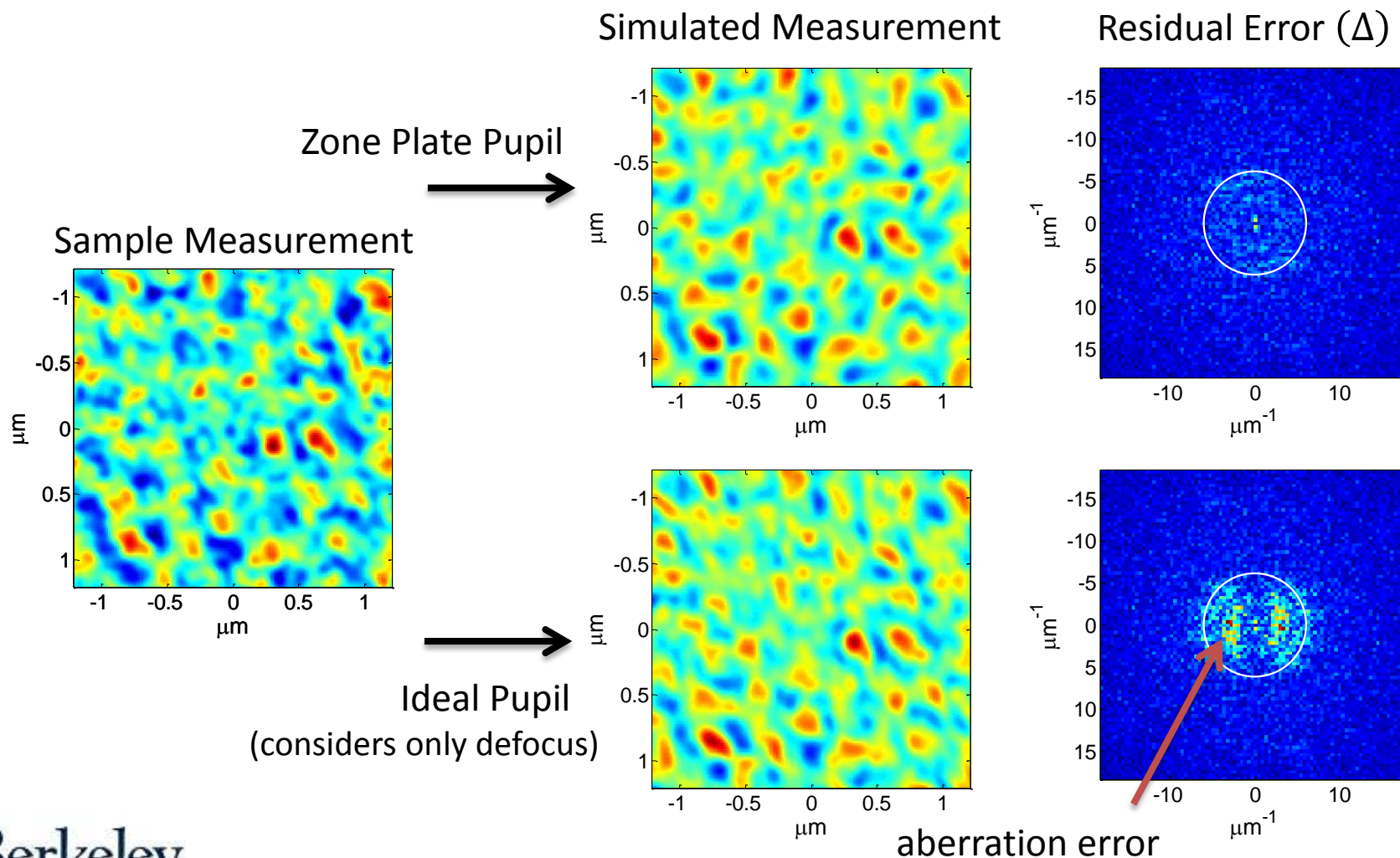
- Small stage drift
- Field dependent illumination

Guessed good parameters

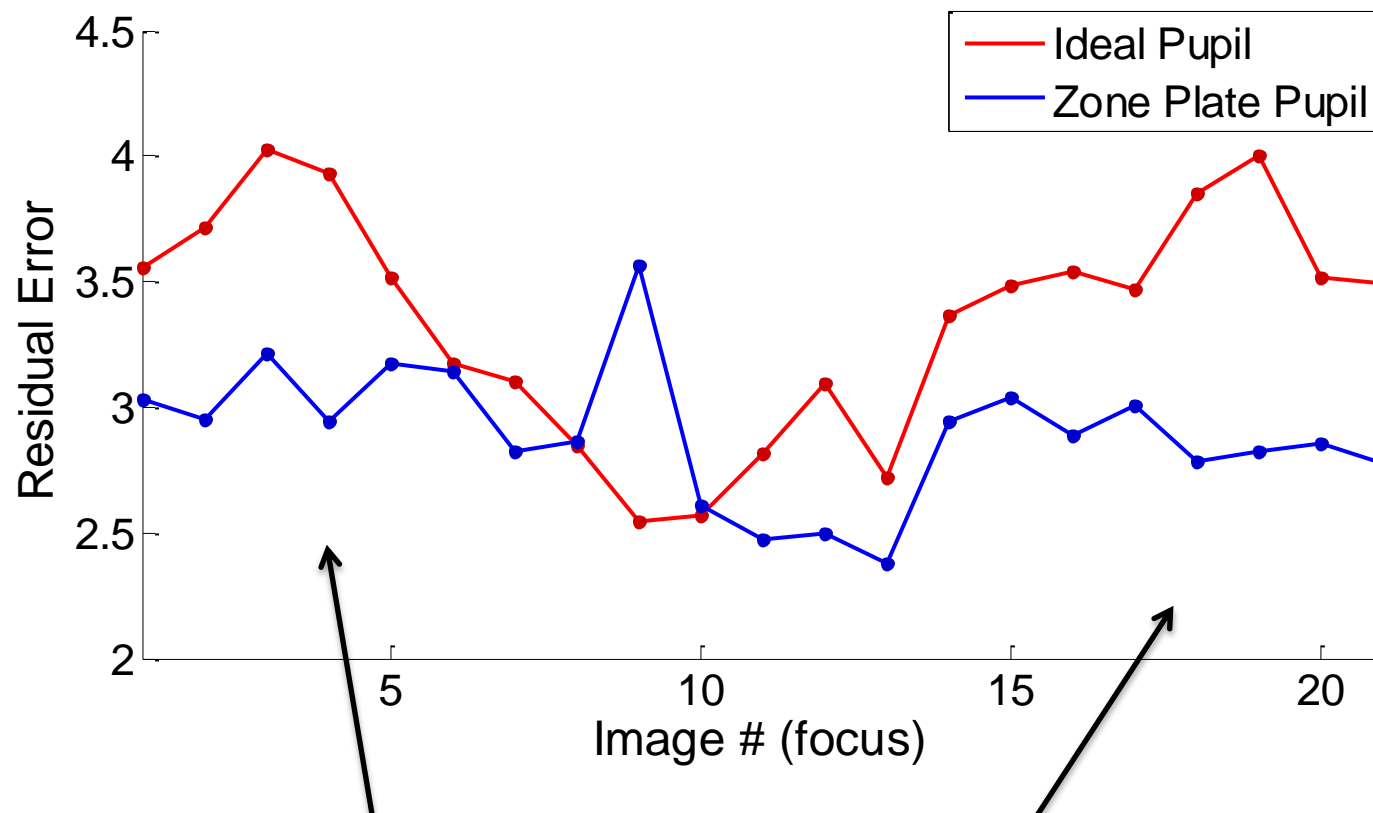
Reduced Residual



Reduced Residual



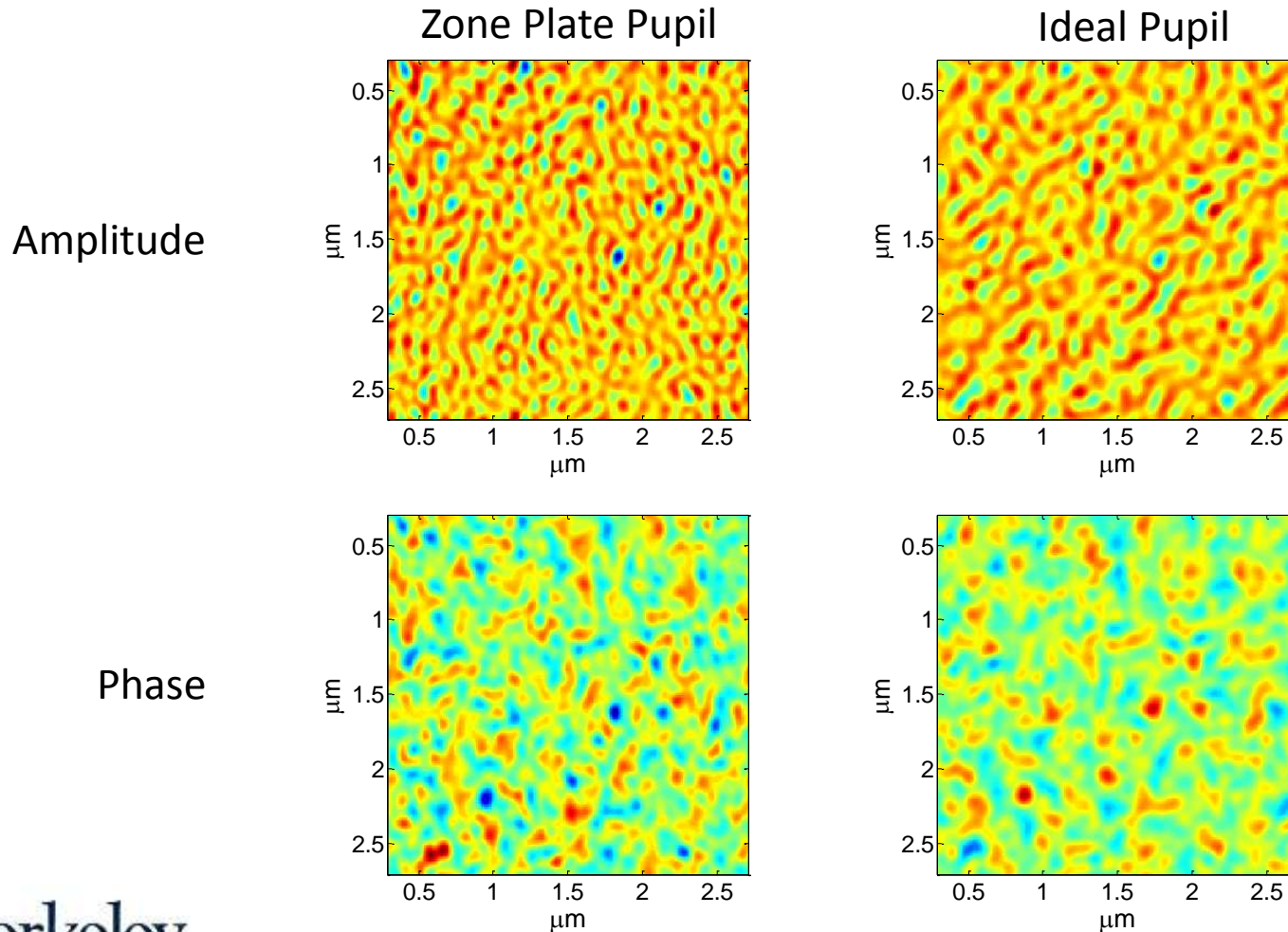
Improved Results with ZP Model



Ideal pupil fits “average aberration” → fits best at center of the stack

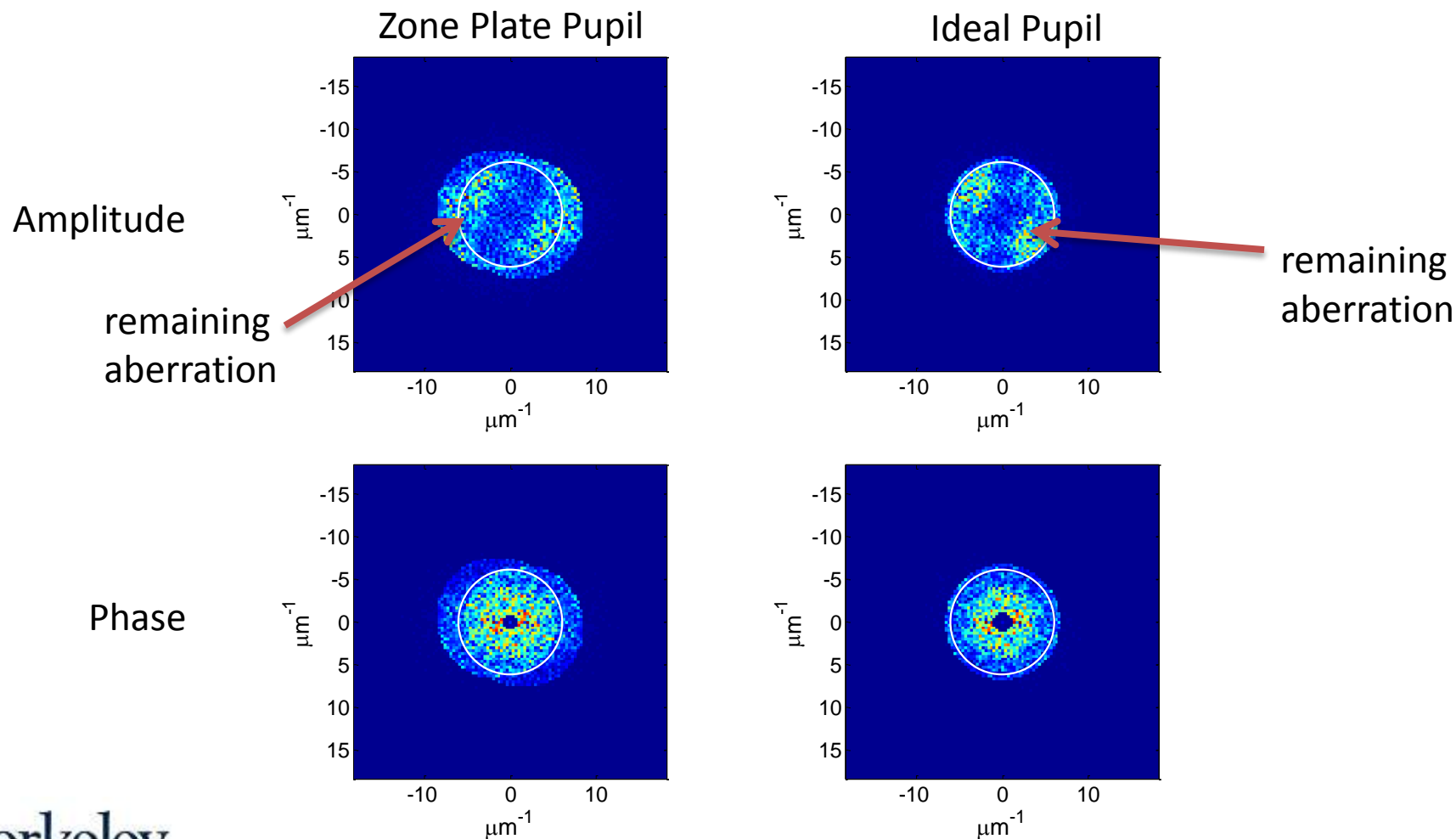
Uncorrected Aberrations Affect the Object

Recovered Object:



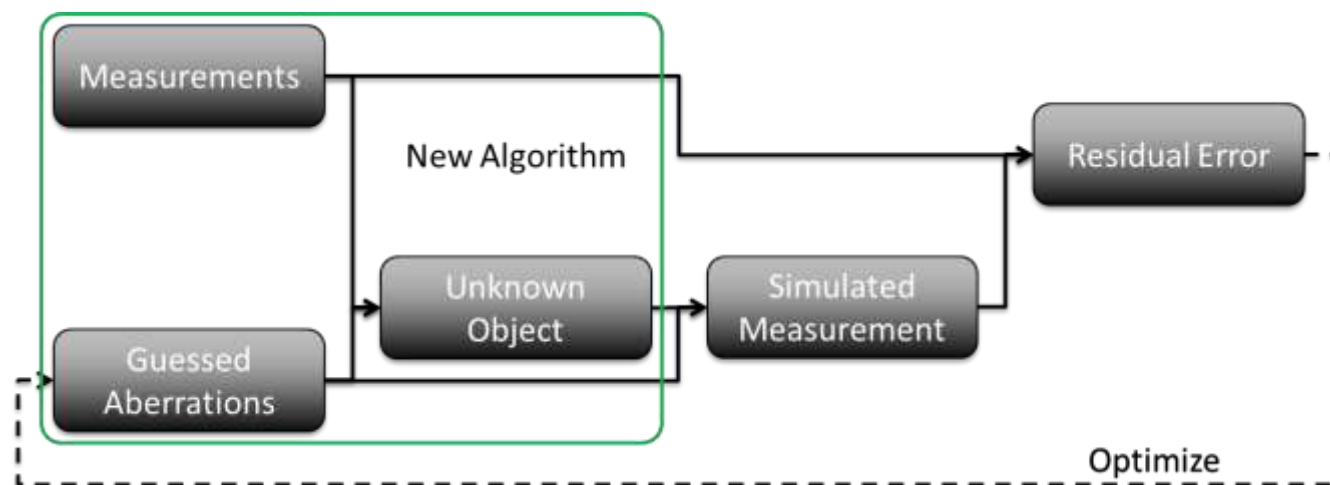
Uncorrected Aberrations Affect the Object

Recovered Object:



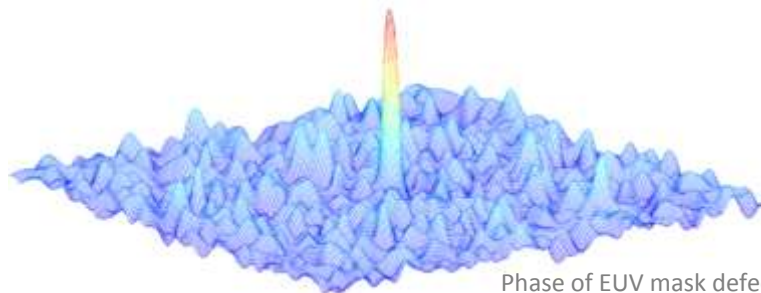
Conclusion

- Presented new algorithm to measure aberrations
 - Unknown test object (ex: EUV mask roughness)
 - Use partial coherence to improve sensitivity
- Used a physical model for the zone plate on SHARP
 - Removed zone plate aberrations
 - Recovered field from aberrated images



Acknowledgement



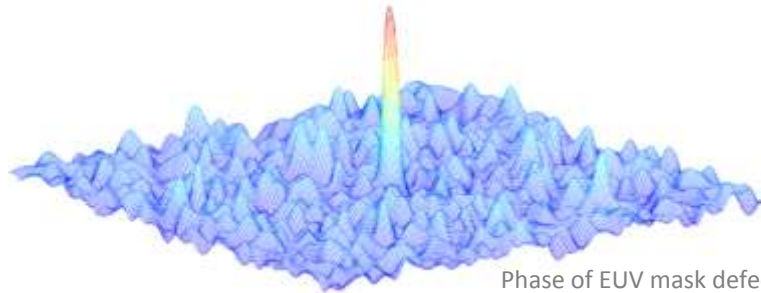


Phase of EUV mask defect

Thank you for your attention!

reneclaus@gmail.com

Berkeley
UNIVERSITY OF CALIFORNIA



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Questions?

reneclaus@gmail.com

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